

# 808nm – high power diode lasers for long term stable pump modules

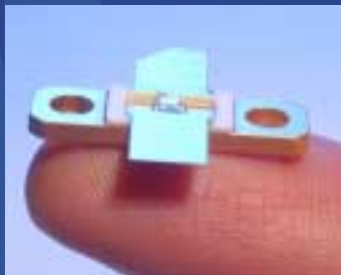
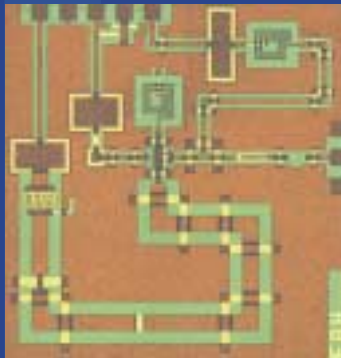
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## outline

- FBH
- Design, technology and properties of single emitters
- Performance of CW laser bars
- QCW pump sources for BepiColombo
- First results for QCW pump sources with higher power and repetition rate (ATLID)
- Summary and outlook

## Facts & Figures



- **Shareholders**
  - State of Berlin / Federal Republic of Germany
- **Founded in**
  - 1992
- **Member / Partner of**
  - Forschungsverbund Berlin e.V.
  - Leibniz Association
  - Technische Universität Berlin
  - Humboldt-Universität zu Berlin
- **Staff**
  - 160 (including 75 scientists & PhD students)
- **Budget / Turnover**
  - 14 M€ (including 5 M€ project revenues)

## Mission of FBH

Applied research and development of microwave & optoelectronic devices, circuits and modules:

Innovations with Microwaves & Light

Market-driven & customer-oriented

- Close cooperation with partners in research and industry serving customers needs
- Part of value chain
- Demonstrators, pilot & small scale production
- Stringent quality management, DIN EN ISO 9001:2000



## Research Topics

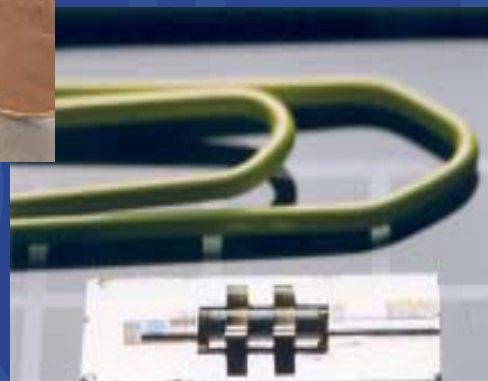
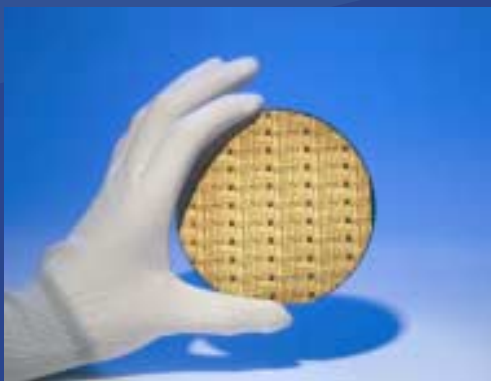
- Microwave components
- Power diode lasers
- UV emitters
- III/V-technologies



## Programs

- Research and Development on microwave & optoelectronic devices, circuits, modules
- Transfer programs
  - Spin-offs and start-ups
  - SMEs
  - Global players
- Services

## value chain



## 808nm diode lasers - basic technology of FBH

### ■ design:

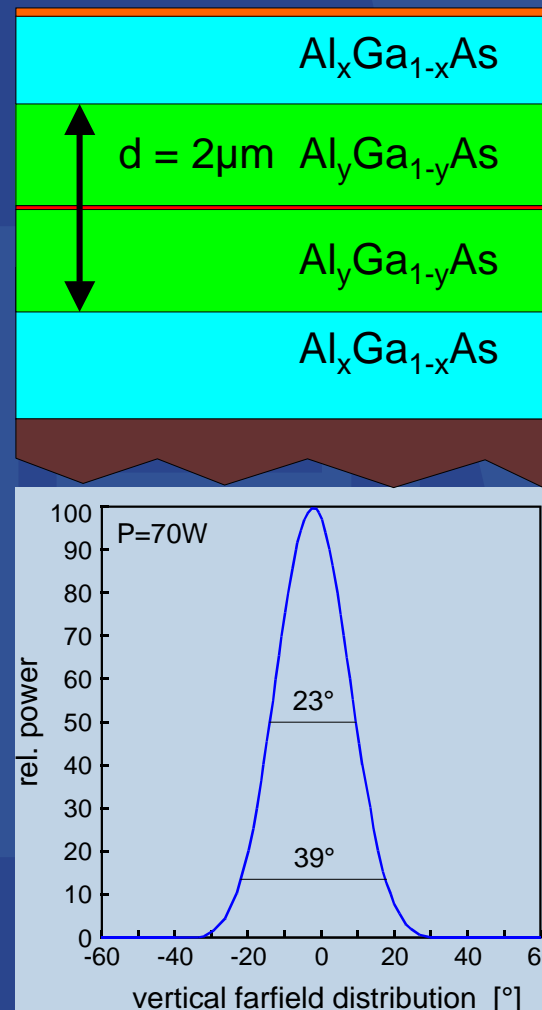
- GaAsP – QW,
- AlGaAs LOC structure ( $x \approx y+0.3$ )
- low vertical divergence

### ■ chip-technology

- MOVPE multi wafer reactor
- process line (full wafer 3")
- passivation after cleaving
- coating by dielectric layers using IBS

### ■ mounting

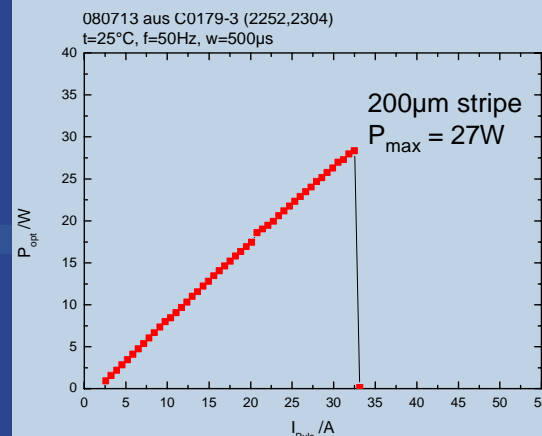
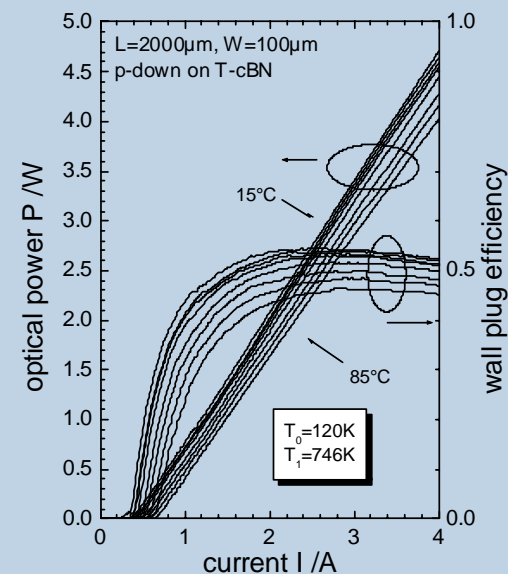
- AuSn soldering of chips
- use of expansion matched submounts
- Au wire bonding



## 808nm diode lasers of FBH – basic data

### typical data of 100 $\mu$ m stripe emitters

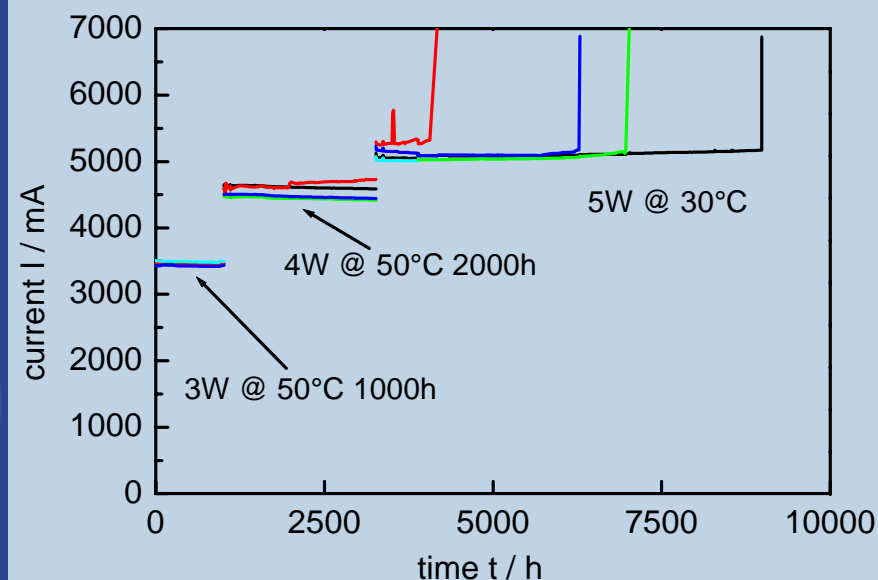
- Threshold current density  
 $\approx 250\text{A/cm}^2$
- Slope efficiency  
 $> 1.2\text{W/A}$
- Temperature stability  
 $> 120\text{K}$
- COD level (500 $\mu$ s, 50Hz)  
 $> 10\text{W}/100\mu\text{m}$
- TM polarisation





## 808nm diode lasers of FBH – basic reliability

- Lifetime test at high facet load
  - Mounting on C-Mount ( $R_{th} \approx 10K/W$ )
- Excellent stability  
40mW /  $\mu m$  stripe width
- failures at 50mW /  $\mu m$  stripe caused by internal defects
- QCW – bar performance determined by mounting issues and homogeneity!
  - Stability of chip material against optical load  
> 50 000h @ 2% duty cycle
  - small chips



## CW – laser diode benches for space suited 808nm pumping modules

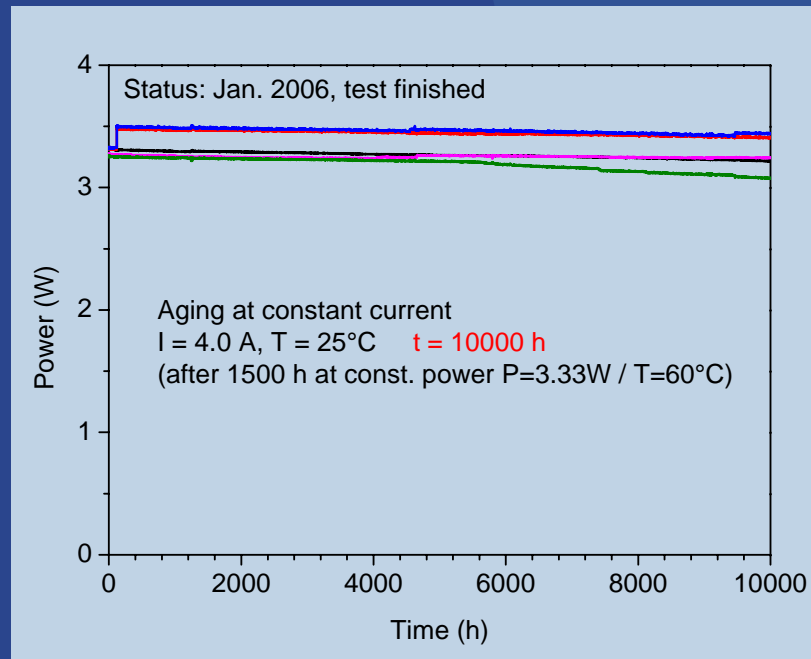
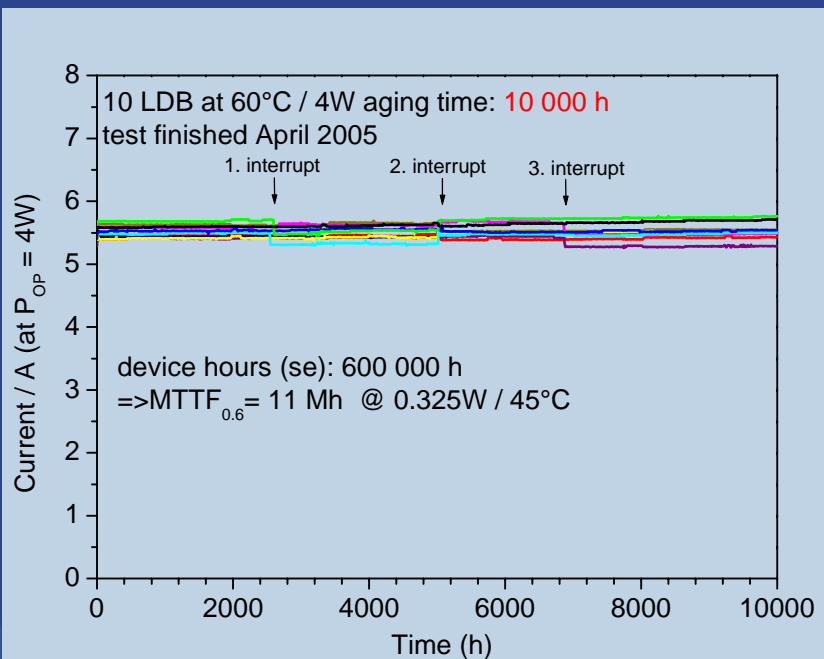
- Projects
  - LCTSX
  - ALADIN
  - GIFTS
  - LTP
  - QSL
- Chip design
  - minibar (chip size <5mm )
  - low fill factor
- Space qualified mounting process
  - expansion matched materials
  - AuSn – solder
  - high precision, robust FAC fixing
  - external spectral stabilization



# Reliability of space suited CW- laser diode benches

4W, 10 000h, 60°C LCTSX

4A, 10 000h, 25°C ALADIN



- Long term test  $\Rightarrow$  reliability  $> 0.99$  4 years at  $P = 1W$  ( $\leq 10mW/\mu m$ )
- Tested mounting scheme
  - temperature cycling
  - mechanical issues

## 808nm – QCW pump sources for Bepi Colombo

### Requirements

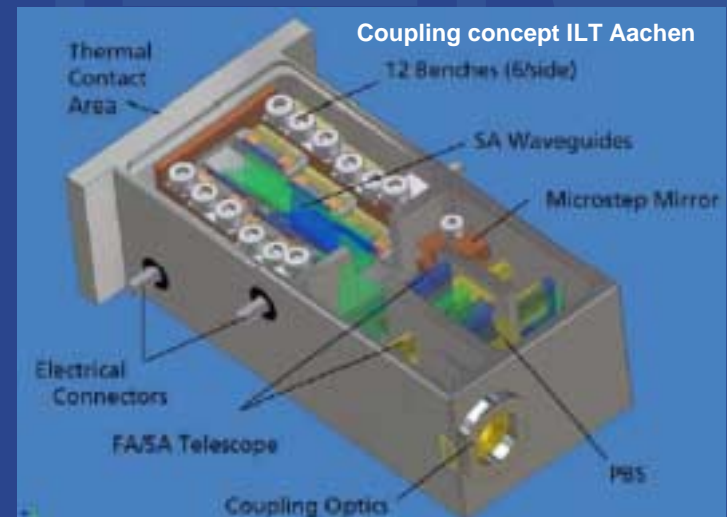
- 700 W usable power (fibre coupled)
- 200µs pulse width,  $\leq 10$ Hz rep. rate
- Long term stability
  - 300 Mio shots
  - about 10 year storage
- $T_{op} = (22 \pm 10) ^\circ\text{C}$
- Environmental conditions (- 45°C ... 65°C)
- small size and low weight

## 808nm – QCW pump sources for Bepi Colombo: chip - design

- design for 70W power / bar (derated power level)
- GaAsP QW
- LOC -structure
- small chip size
  - facet load 20mW/ $\mu\text{m}$
  - 4.5 mm emitting aperture ( half of standard bar!)
  - 1.5 mm resonator length
  - 35 emitter, filling factor 70%
- conversion efficiency of chip  $\approx 60\%$
- wavelength  $(807 \pm 2)\text{nm}$

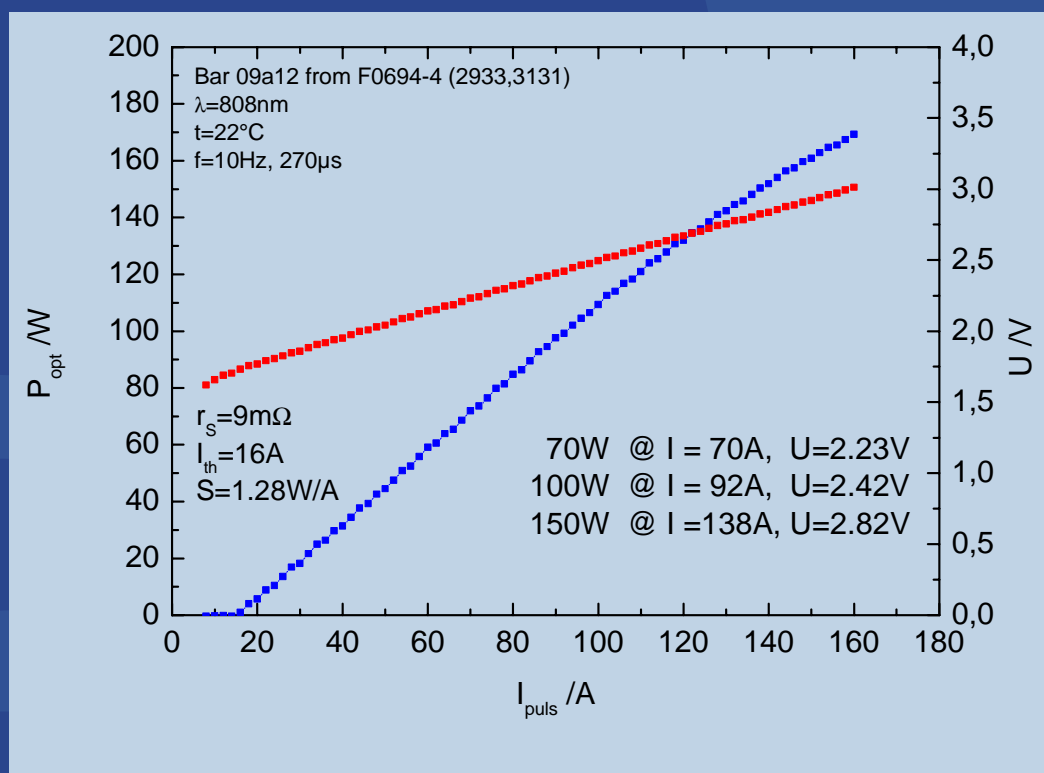
## 808nm – QCW pump sources for Bepi Colombo: mounting issues

- no dense vertical stacks
- Single devices on 10x10mm<sup>2</sup> footprint
- Expansion matched materials
- AuSn soldering (chip, n-contact plate)
- Wire bonding
- Approved FAC fixing



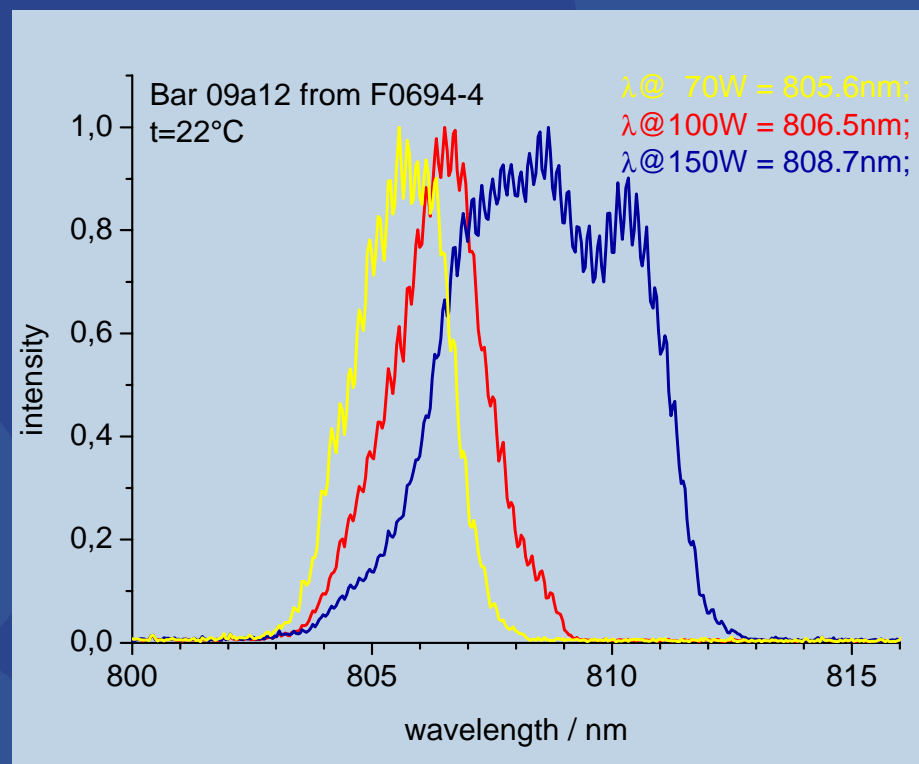
## 808nm – QCW pump sources for Bepi Colombo : L-U-I curves

- $I_{th} \approx 15 \text{ A}$
- $I_{op} \approx 70 \text{ A @ } 70 \text{ W}$
- Slope  $\eta_d \geq 1.25 \text{ W/A}$
- conversion efficiency  
 $\eta_c \approx 50\% \text{ @ } 70 \text{ W}$
- Series resistance  
 $R_s \approx 9 \text{ m}\Omega$
- COD level  $P_{max} > 250 \text{ W} !$   
(  $> 80 \text{ mW}/\mu\text{m}$  )



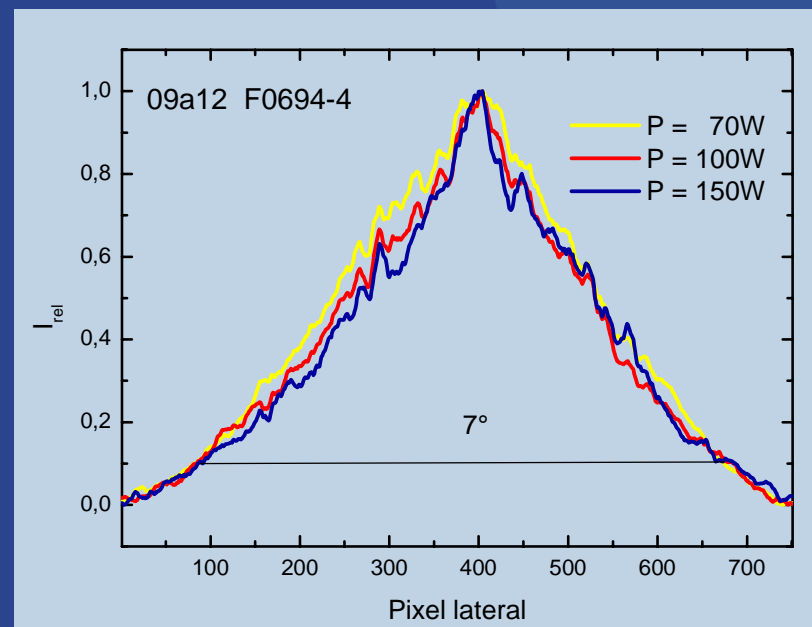
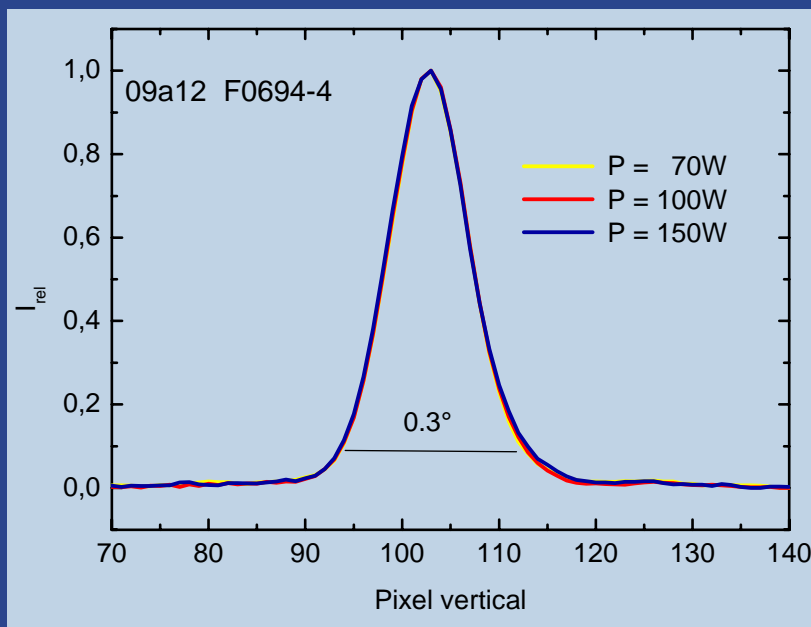
## 808nm – QCW pump sources for Bepi Colombo : spectral

- spectral peak 806nm
- spectral width (95% power) < 4nm
- additional modulation by FAC
- wavelength shift determined by temperature





## 808nm – QCW pump sources for Bepi Colombo : beam profile



- Fast axis with collimation
- slow axis

$$\theta_{\perp} < 5\text{mrad} (>95\% \text{ power})$$

$$\theta_{||} < 120\text{mrad} (>95\% \text{ power})$$

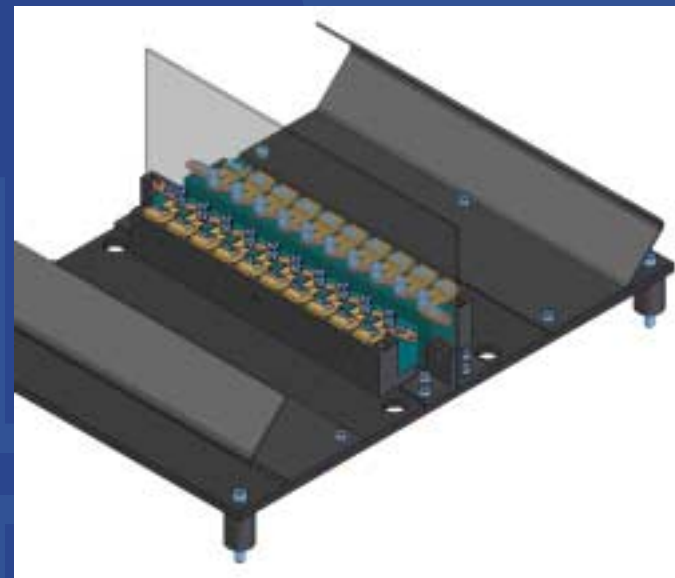
## Preliminary life test for bars Bepi Colombo

### ■ Purpose

- demonstration of feasibility
- determination of screening parameters

### ■ Conditions

- 10 devices (348 emitters)  
(selected by L-I curve + 300h burn in at 100A / 10Hz)
- constant current  $I_{op} = 142A$  ( $P > 150 W$ )
- 20 Hz
- 1300 h  $\approx 93.6$  Mshots



## Results of life test

Parameter	1	2	3	4	5	6	7	8	9	10
$I_{th}$ /A	13.6 13.7	14.7 14.8	13.9 15.1	13.0 13.2	14.6 15.1	14.0 14.6	13.6 15.6	13.2 13.8	14.0 13.7	13.9 14.2
$I_{op}$ (100W) /A	92 92	94 100	92 92	92 104	93 92	94 100	94 100	92 105	92 96	92 94
$\Delta\lambda$ /nm	0	0.5	0.1	-1.3	0	0.2	0.2	0.7	1.1	0.1
Emitter failure	0	1*	0	7	0	2	1*	6	0	0

- no bar failed (EOL – current limit  $I_{op} < 110A$  @100W)
- Long term stable spectral behaviour  $\Delta\lambda < 1nm$
- Reliability  $> 0.999$  per bar for  $P_{op} = 70W$  ,  $3.15 \times 10^8$  shots (10Hz, 1 year)
  - calculation based on random single emitter failures,
  - acceleration by power  $(P/P_{op})^{2.3}$   
(2.3 standard value of 808nm devices)

## 808nm - QCW – pump sources for higher average power (ATLAS)

### ▪ Requirements

- 808nm
- space qualification issues similar to Bepi Colombo
- output power  $\geq 100\text{W}$  per bar
- repetition rate  $\approx 100\text{Hz}$
- reliability 10 Gshot

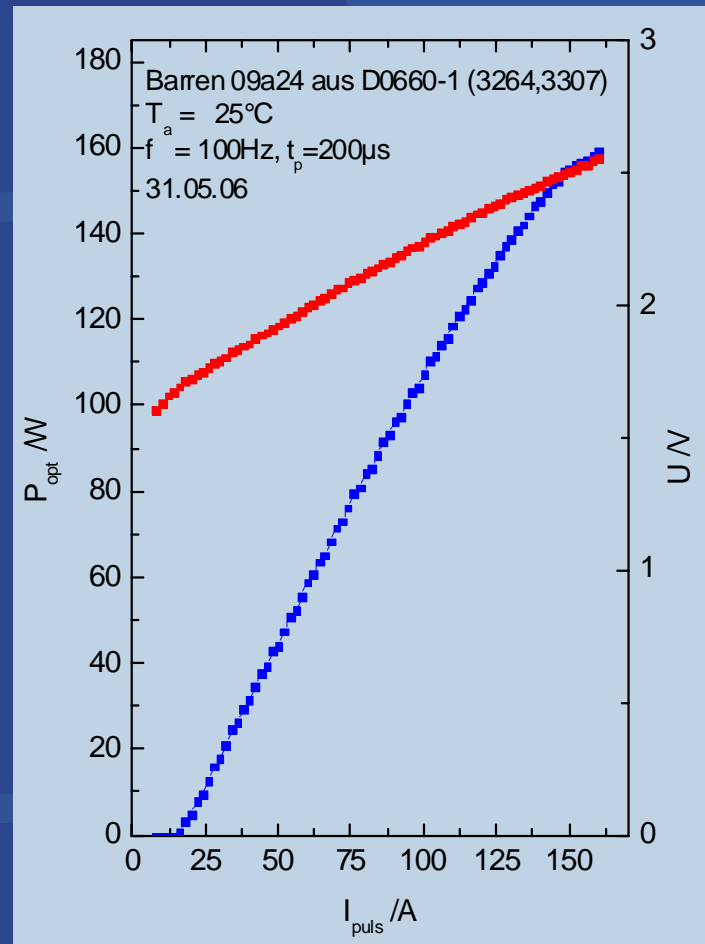


- improved chip design for slightly higher peak power
- Improved mounting scheme designed for 10x-higher average power

## 808nm - QCW – pump sources for higher average power (ATLAS) first results I

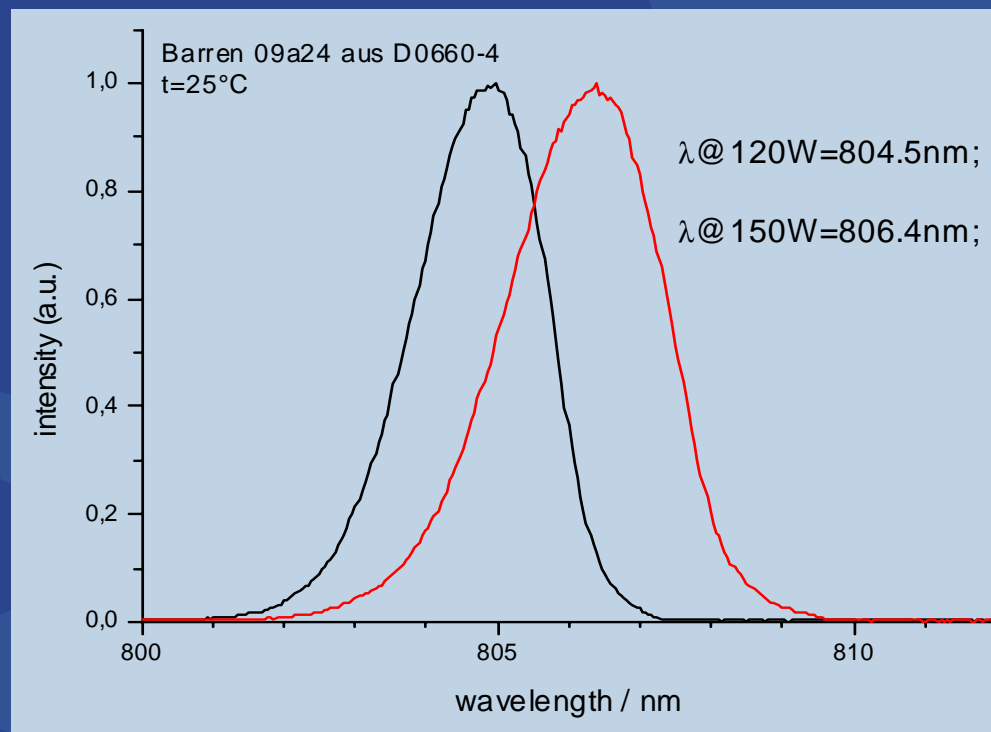
100W power / bar

- GaAsP QW
- improved layer - structure
- chip size
  - facet load 30mW/ $\mu\text{m}$
  - 4.5 mm emitting aperture
  - 1.5 mm resonator length
  - 35 emitter, filling factor 70%
- conversion efficiency of chip  $\approx 65\%$
- wavelength  $(807 \pm 2)\text{nm}$



## 808nm - QCW – pump sources for higher average power (ATLAS) first results II

- spectral peak at 804.5nm
- enabling  $\lambda$  - tuning  
by CW bias current
- spectral width < 4nm  
(95% power)
- wavelength shift  
determined by temperature



## Summary – 808nm QCW pump lasers

- **electro – optical performance**

- $I_{op} < 100A @ 100W$  (  $\approx 70A @ 70W$  )
- $P_{cod} > 3x P_{op}(70W)$
- $\lambda \approx (805...806)nm$ ,  $\Delta \lambda (95\%) \leq 5nm @ P_{op}$
- far field  $\Theta_{\perp} < 5mrad$ ,  $\Theta_{\parallel} \approx 120mrad @ 95\%$
- $U_{op} \approx 2.4 V$  at 100A

- **mounting scheme**

- proved design for 10Hz
- thermal cycling between – 45°C and 65°C

- **reliability > 0.999 (70W, 1 year, 10Hz ) expected**

## outlook

- To do - short range
  - screening procedure
  - verification of reliability
  - extended life time tests (acceleration!?)
  - reducing series resistance
  
- Improvement opportunities chip - longer range
  - optimised design (pumping scheme)
  - wavelength stabilisation by internal gratings (DFB /DBR)

